In the Claims

Please replace all prior versions, and listings, of claims in the application with the following list of claims:

1. (Previously Presented) An integrated circuit comprising a buried layer of determined conductivity type in a plane substantially parallel to a plane of a main circuit surface, wherein a median portion of said buried layer is filled with a metal-type material.

2. (Original) The integrated circuit of claim 1, wherein the buried layer is a sub-collector layer of a bipolar transistor.

3. (Original) The integrated circuit of claim 1, wherein the metal-type material is titanium nitride.

4. (Canceled)

5. (Canceled)

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Currently Amended) An integrated circuit comprising a buried layer of determined conductivity type disposed in a plane substantially parallel to a surface of the integrated circuit, wherein a metal-type material is disposed within at least a portion of the buried layer ~~includes a metal-type material~~.

10. (Previously Presented) The integrated circuit of claim 9, wherein the metal-type material forms a core of the buried layer.

11. (Currently Amended) The integrated circuit of claim [[1]] 9, wherein the buried layer is a sub-collector layer of a bipolar transistor.

12. (Previously Presented) The integrated circuit of claim 1, wherein the metal-type material is chosen from the group consisting of conductive oxides, metal silicides, titanium nitride, tantalum nitride, or copper.

13. (New) The integrated circuit of claim 9, wherein the metal-type material is chosen from the group consisting of conductive oxides, metal silicides, titanium nitride, tantalum nitride, or copper.

14. (New) An integrated circuit, comprising:

a buried layer of a first conductivity type;

a region of metal-type material disposed within at least a portion of the buried layer, the region having a vertical extent and a horizontal extent greater than the vertical extent, the horizontal extent being parallel to a surface of the integrated circuit.

15. (New) The integrated circuit of claim 14, wherein the buried layer is a sub-collector layer of a bipolar transistor.

16. (New) The integrated circuit of claim 14, wherein the metal-type material is titanium nitride.

17. (New) The integrated circuit of claim 14, wherein the metal-type material is chosen from the group consisting of conductive oxides, metal silicides, titanium nitride, tantalum nitride, or copper.

18. (New) The integrated circuit of claim 14, wherein the region is a core of the buried layer.

19. (New) The integrated circuit of claim 14, wherein a conductivity of the metal-type material is greater than a conductivity of the buried layer.

20. (New) The integrated circuit of claim 14, further comprising a collector well comprising a material of composition substantially a same composition as the metal-type material.

21. (New) The integrated circuit of claim 14, further comprising a collector well that contacts the metal-type material.

22. (New) The integrated circuit of claim 14, further comprising an insulating wall extending from the surface to at least a depth of the buried layer.